



2SA1981SF

PNP Silicon Transistor

Description

- Audio power amplifier application

Features

- High h_{FE} : $h_{FE}=100\sim320$
- Complementary pair with 2SC5344SF

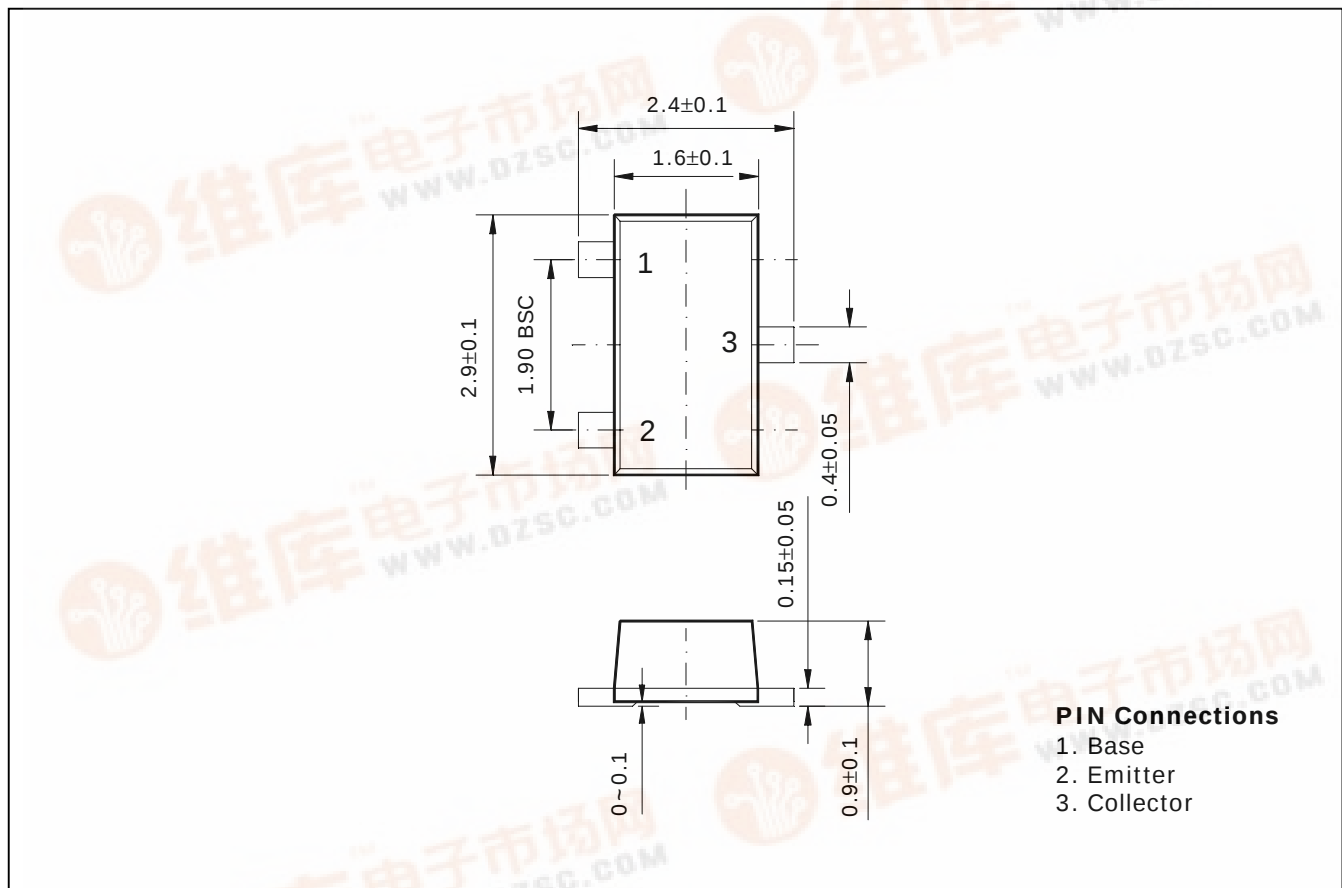
Ordering Information

Type NO.	Marking	Package Code
2SA1981SF	EA□	SOT-23F

□ : h_{FE} rank

Outline Dimensions

unit : mm



2SA1981SF

Absolute maximum ratings

(Ta=25°C)

Characteristic	Symbol	Ratings	Unit
Collector-Base voltage	V_{CBO}	-35	V
Collector-Emitter voltage	V_{CEO}	-30	V
Emitter-Base voltage	V_{EBO}	-5	V
Collector current	I_C	-800	mA
Collector dissipation	P_C	200	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ 150	°C

Electrical Characteristics

(Ta=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base breakdown voltage	BV_{CBO}	$I_C = -500\mu A, I_E = 0$	-35	-	-	V
Collector-Emitter breakdown voltage	BV_{CEO}	$I_C = -1mA, I_B = 0$	-30	-	-	V
Emitter-Base breakdown voltage	BV_{EBO}	$I_E = -50\mu A, I_C = 0$	-5	-	-	V
Collector cut-off current	I_{CBO}	$V_{CB} = -35V, I_E = 0$	-	-	-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$	-	-	-0.1	μA
DC current gain	h_{FE}^*	$V_{CE} = -1V, I_C = -100mA$	100	-	320	-
Collector-Emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -20mA$	-	-	-0.5	V
Transition frequency	f_T	$V_{CE} = -5V, I_E = 10mA$	-	120	-	MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	-	19	-	pF

* : h_{FE} rank / O : 100~200, Y : 160~320

Electrical Characteristic Curves

Fig. 1 P_C - T_a

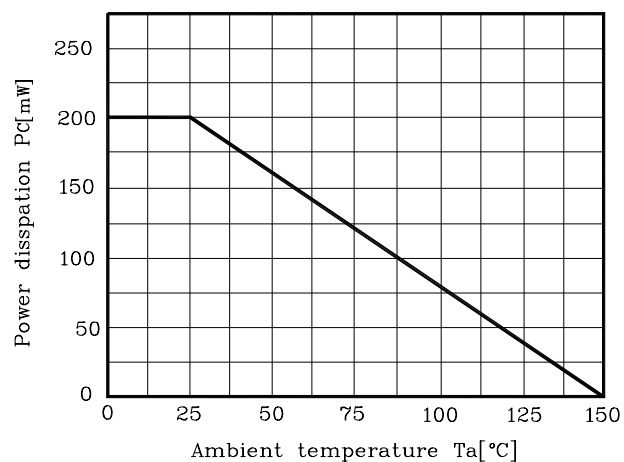


Fig. 2 I_C - V_{BE}

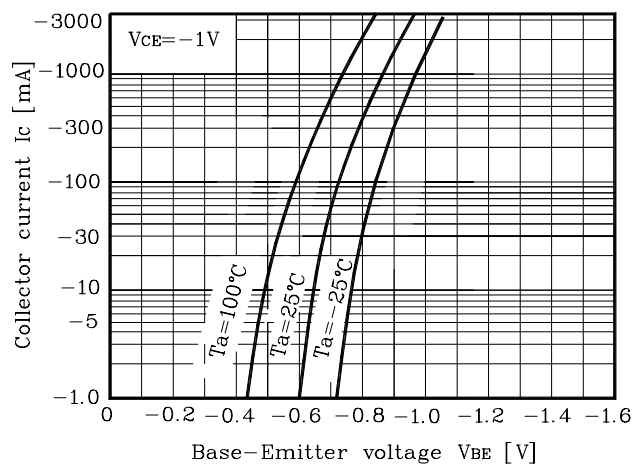


Fig. 3 I_C - V_{CE}

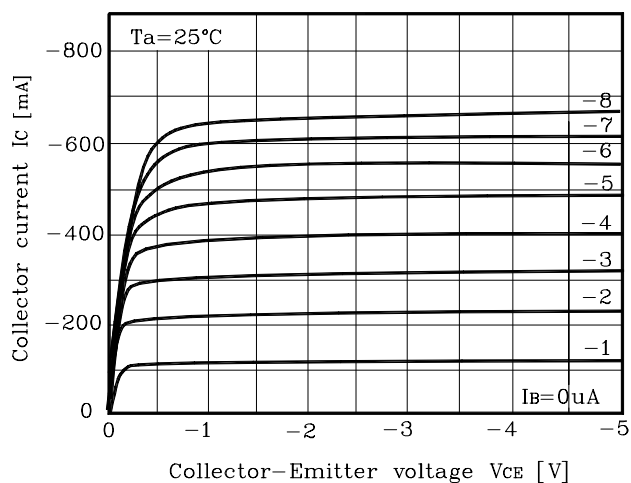


Fig. 4 h_{FE} - I_C

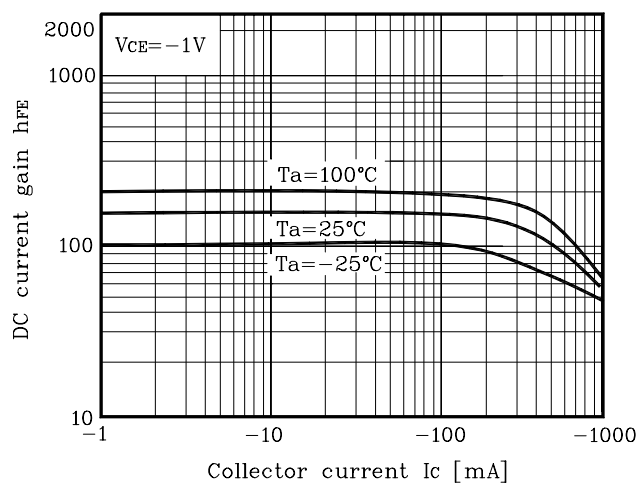


Fig. 5 $V_{CE(SAT)}$ - I_C

